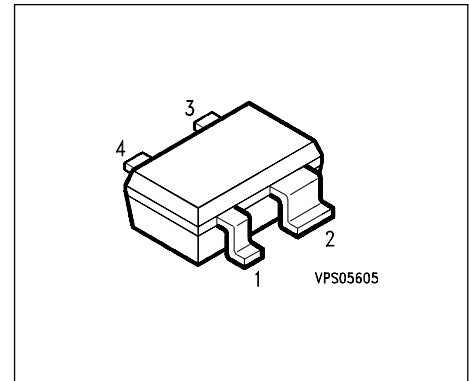


NPN Silicon RF Transistor

- For low noise, low distortion broadband amplifiers in antenna and telecommunications systems up to 1.5GHz at collector currents from 20mA to 80mA
- Power amplifier for DECT and PCN systems
- $f_T = 7.5\text{GHz}$
 $F = 1.5\text{ dB at } 900\text{MHz}$



ESD: Electrostatic discharge sensitive device, observe handling precaution!

| Type | Marking | Ordering Code | Pin Configuration | | | | Package |
|----------|---------|---------------|-------------------|-------|-------|-------|---------|
| BFP 196W | RI5 | Q62702-F1576 | 1 = E | 2 = C | 3 = E | 4 = B | SOT-343 |

Maximum Ratings

| Parameter | Symbol | Values | Unit |
|--|-----------|----------------|------------------|
| Collector-emitter voltage | V_{CEO} | 12 | V |
| Collector-emitter voltage | V_{CES} | 20 | |
| Collector-base voltage | V_{CBO} | 20 | |
| Emitter-base voltage | V_{EBO} | 2 | |
| Collector current | I_C | 100 | mA |
| Base current | I_B | 12 | |
| Total power dissipation $T_S \leq 69\text{ }^\circ\text{C}$ | P_{tot} | 700 | mW |
| Junction temperature | T_j | 150 | |
| Ambient temperature | T_A | - 65 ... + 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | - 65 ... + 150 | |

Thermal Resistance

| | | | |
|--|------------|------------|-----|
| Junction - soldering point ¹⁾ | R_{thJS} | ≤ 115 | K/W |
|--|------------|------------|-----|

1) T_S is measured on the collector lead at the soldering point to the pcb.

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

| Parameter | Symbol | Values | | | Unit |
|---|---------------|--------|------|------|---------------|
| | | min. | typ. | max. | |
| DC Characteristics | | | | | |
| Collector-emitter breakdown voltage $I_C = 1 \text{ mA}, I_B = 0$ | $V_{(BR)CEO}$ | 12 | - | - | V |
| Collector-emitter cutoff current $V_{CE} = 20 \text{ V}, V_{BE} = 0$ | I_{CES} | - | - | 100 | μA |
| Collector-base cutoff current $V_{CB} = 10 \text{ V}, I_E = 0$ | I_{CBO} | - | - | 100 | nA |
| Emitter-base cutoff current $V_{EB} = 1 \text{ V}, I_C = 0$ | I_{EBO} | - | - | 1 | μA |
| DC current gain $I_C = 50 \text{ mA}, V_{CE} = 8 \text{ V}$ | h_{FE} | 50 | 100 | 200 | - |

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

| Parameter | Symbol | Values | | | Unit |
|---|-----------------|--------|--------------|------|------|
| | | min. | typ. | max. | |
| AC Characteristics | | | | | |
| Transition frequency $I_C = 70\text{ mA}$, $V_{CE} = 8\text{ V}$, $f = 500\text{ MHz}$ | f_T | 5 | 7.5 | - | GHz |
| Collector-base capacitance $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$ | C_{cb} | - | 1 | 1.4 | pF |
| Collector-emitter capacitance $V_{CE} = 10\text{ V}$, $f = 1\text{ MHz}$ | C_{ce} | - | 0.36 | - | |
| Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$ | C_{eb} | - | 3.7 | - | |
| Noise figure $I_C = 20\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{\text{Sopt}}$ $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$ | F | - | 1.5 2.5 | - | dB |
| Power gain ²⁾ $I_C = 50\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{\text{Sopt}}$ $Z_L = Z_{\text{Lopt}}$ $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$ | G_{ma} | - | 17.5 11.5 | - | |
| Transducer gain $I_C = 50\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_L = 50\ \Omega$ $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$ | $ S_{21e} ^2$ | - | 12.5 6.5 | - | |

2) $G_{\text{ma}} = |S_{21}/S_{12}| (k - (k^2 - 1)^{1/2})$

SPICE Parameters (Gummel-Poon Model, Berkeley-SPICE 2G.6 Syntax) :

Transistor Chip Data

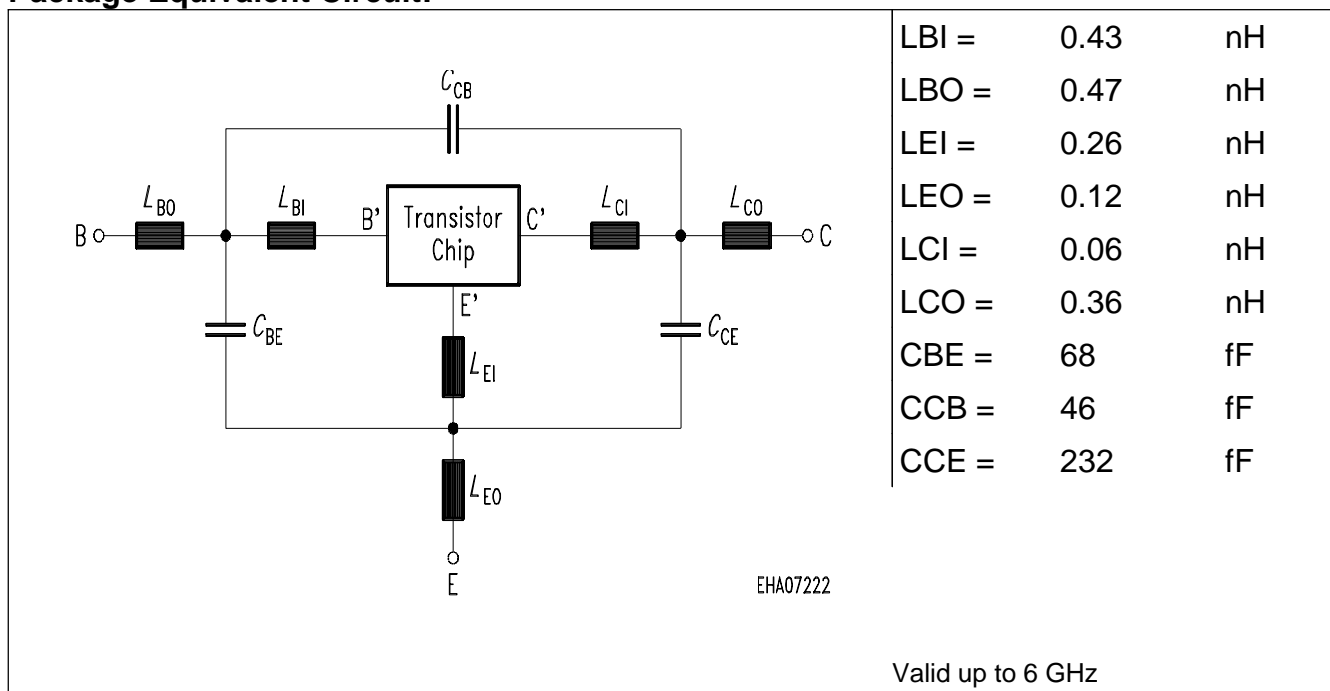
| | | | | | | | | |
|-------|---------|----------|-------|----------|----------|--------|----------|----------|
| IS = | 1.7264 | fA | BF = | 125 | - | NF = | 0.80012 | - |
| VAF = | 20 | V | IKF = | 0.4294 | A | ISE = | 119.22 | fA |
| NE = | 1.1766 | - | BR = | 10.584 | - | NR = | 0.94288 | - |
| VAR = | 3.8128 | V | IKR = | 0.019511 | A | ISC = | 4.8666 | fA |
| NC = | 0.88299 | - | RB = | 1.2907 | Ω | IRB = | 0.084011 | mA |
| RBM = | 1 | Ω | RE = | 0.75103 | Ω | RC = | 0.27137 | Ω |
| CJE = | 13.325 | fF | VJE = | 0.7308 | V | MJE = | 0.33018 | - |
| TF = | 23.994 | ps | XTF = | 0.44322 | - | VTF = | 0.1 | V |
| ITF = | 1.9775 | mA | PTF = | 0 | deg | CJC = | 1667 | fF |
| VJC = | 0.73057 | V | MJC = | 0.3289 | - | XCJC = | 0.29998 | - |
| TR = | 2.2413 | ns | CJS = | 0 | fF | VJS = | 0.75 | V |
| MJS = | 0 | - | XTB = | 0 | - | EG = | 1.11 | eV |
| XTI = | 3 | - | FC = | 0.50922 | - | TNOM | 300 | K |

All parameters are ready to use, no scaling is necessary.

Extracted on behalf of SIEMENS Small Signal Semiconductors by:
Institut für Mobil- und Satellitenfunktechnik (IMST)

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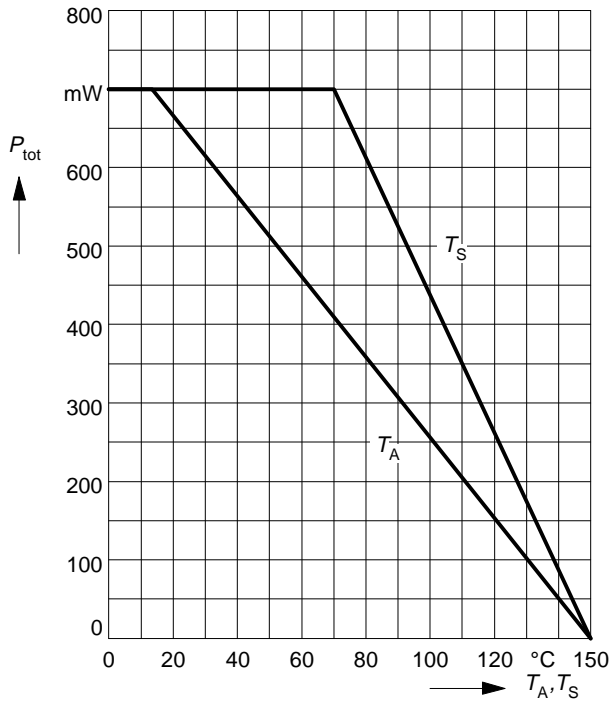
Package Equivalent Circuit:



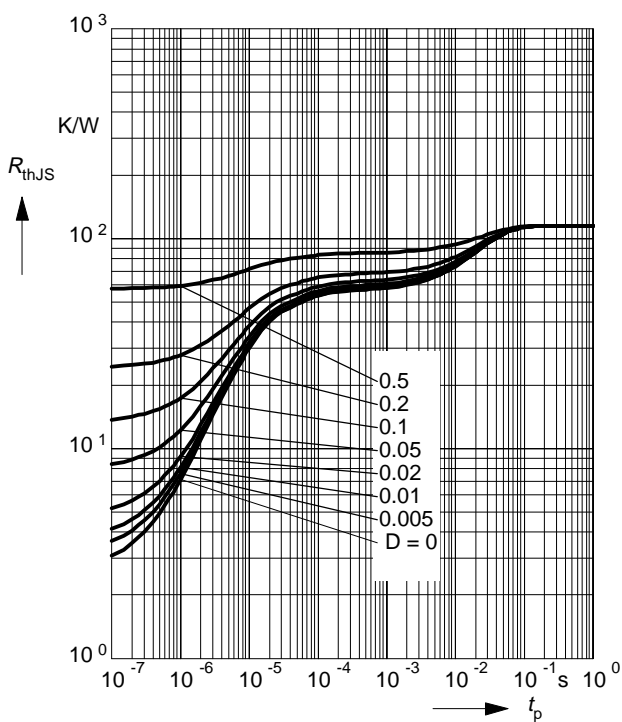
For examples and ready to use parameters please contact your local Siemens distributor or sales office to obtain a Siemens CD-ROM or see Internet: <http://www.siemens.de/Semiconductor/products/35/35.htm>

Total power dissipation $P_{tot} = f(T_A^*, T_S)$

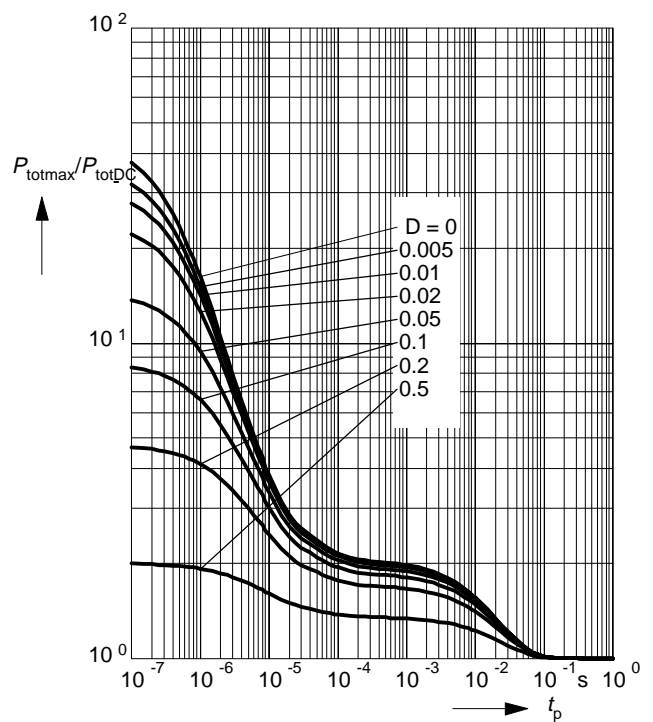
* Package mounted on epoxy



Permissible Pulse Load $R_{thJS} = f(t_p)$

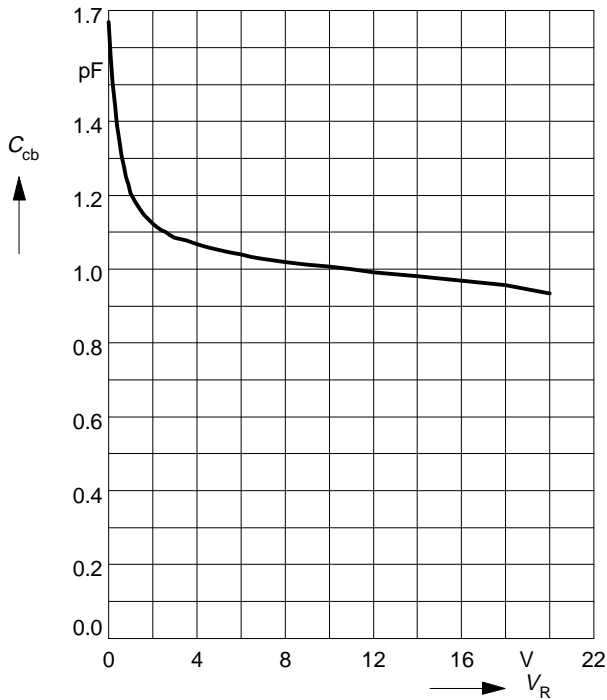


Permissible Pulse Load $P_{totmax}/P_{totDC} = f(t_p)$



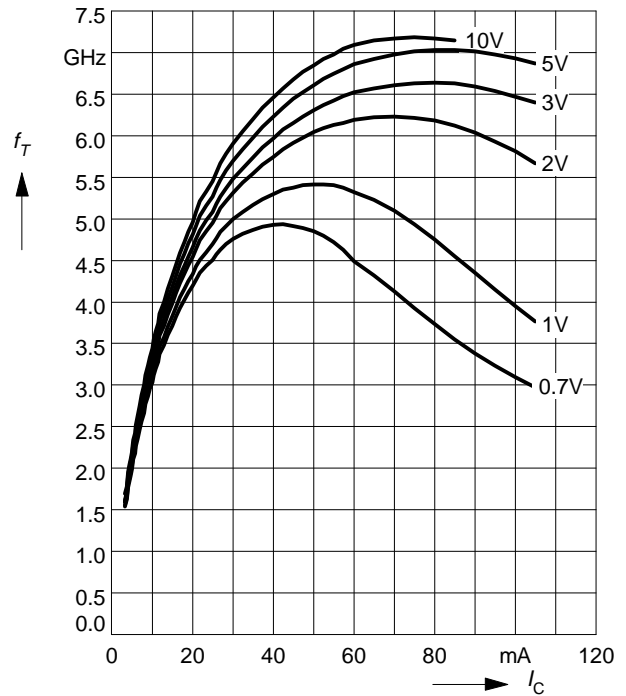
Collector-base capacitance $C_{cb} = f(V_{CB})$

$V_{BE} = v_{be} = 0, f = 1\text{MHz}$



Transition frequency $f_T = f(I_C)$

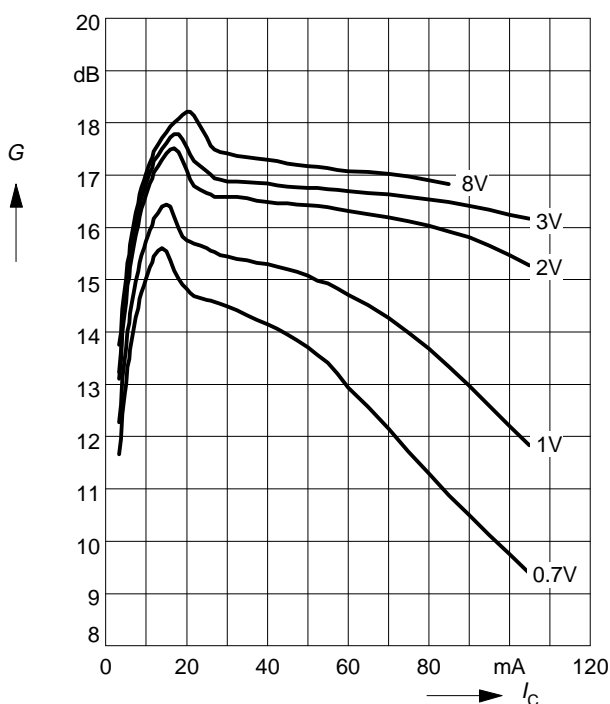
$V_{CE} = \text{Parameter}$



Power Gain $G_{ma}, G_{ms} = f(I_C)$

$f = 0.9\text{GHz}$

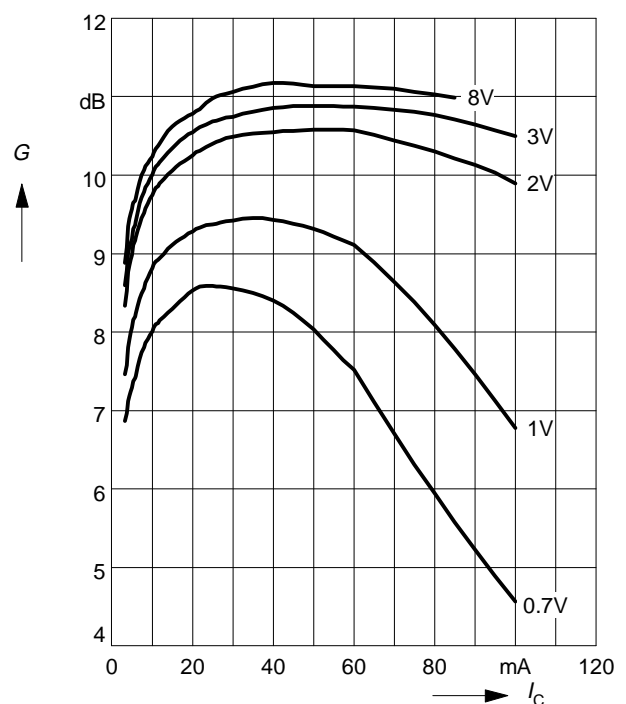
$V_{CE} = \text{Parameter}$



Power Gain $G_{ma}, G_{ms} = f(I_C)$

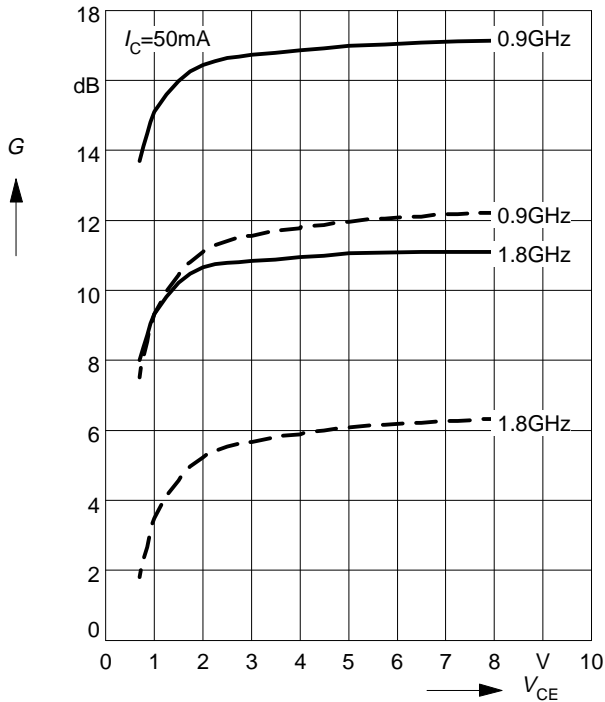
$f = 1.8\text{GHz}$

$V_{CE} = \text{Parameter}$



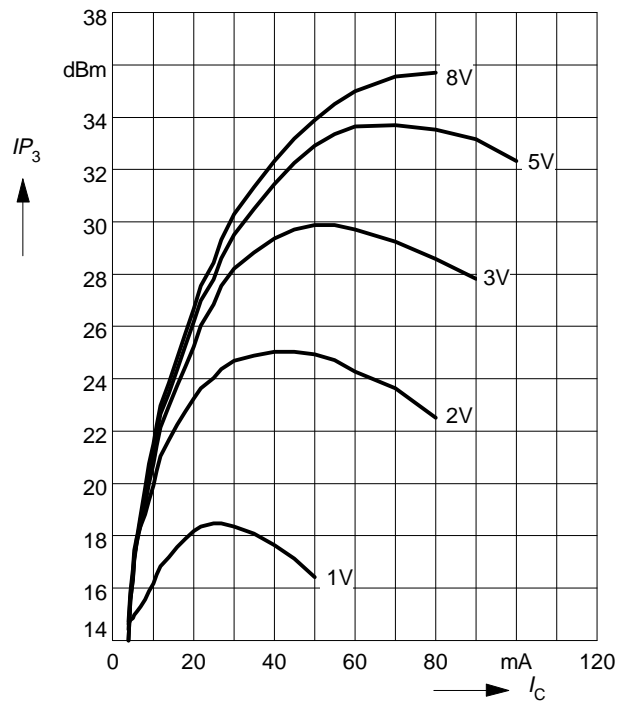
Power Gain $G_{ma}, G_{ms} = f(V_{CE})$: _____
 $|S_{21}|^2 = f(V_{CE})$: -----

f = Parameter



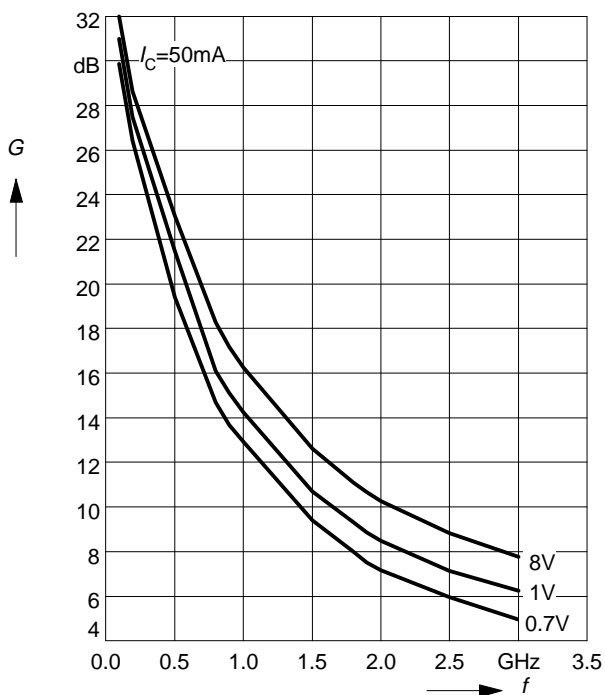
Intermodulation Intercept Point $IP_3 = f(I_C)$
 (3rd order, Output, $Z_S = Z_L = 50\Omega$)

V_{CE} = Parameter, $f = 900\text{MHz}$



Power Gain $G_{ma}, G_{ms} = f(f)$

V_{CE} = Parameter



Power Gain $|S_{21}|^2 = f(f)$

V_{CE} = Parameter

